

TOSHIBA Transistor Silicon NPN·PNP Epitaxial Type  
(PCT process) (Bias Resistor Built-in Transistor)

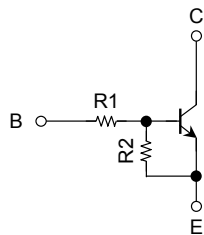
# RN4987FS

Switching, Inverter Circuit, Interface Circuit and  
Driver Circuit Applications

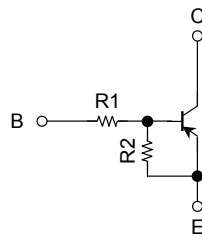
- Two devices are incorporated into a fine pitch small mold (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and saves assembly cost.

## Equivalent Circuit and Bias Resistor Values

**Q1**



**Q2**

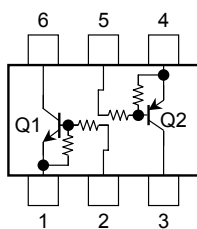


R1: 10 kΩ

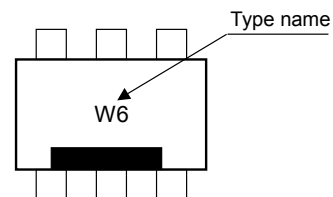
R2: 47 kΩ

(Q1, Q2 common)

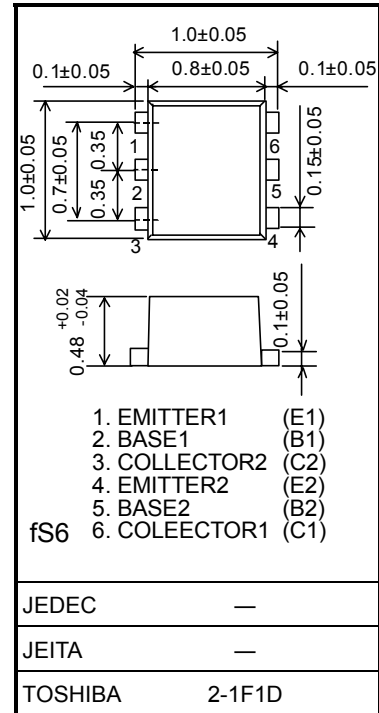
## Equivalent Circuit (top view)



## Marking



Unit: mm



Weight: 0.001g (typ.)

**Maximum Ratings (Ta = 25°C) (Q1)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	20	V
Collector-emitter voltage	V <sub>CE0</sub>	20	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>C</sub>	50	mA

**Maximum Ratings (Ta = 25°C) (Q2)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-20	V
Collector-emitter voltage	V <sub>CE0</sub>	-20	V
Emitter-base voltage	V <sub>EB0</sub>	-6	V
Collector current	I <sub>C</sub>	-50	mA

**Maximum Ratings (Ta = 25°C) (Q1, Q2 common)**

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> (Note)	50	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating

## Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 20\text{ V}, I_E = 0$	—	—	100	nA
	$I_{CEO}$	$V_{CE} = 20\text{ V}, I_B = 0$	—	—	500	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 6\text{ V}, I_C = 0$	0.088	—	0.131	mA
DC current gain	$h_{FE}$	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	120	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	—	0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = 0.2\text{ V}, I_C = 5\text{ mA}$	0.7	—	1.5	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ mA}$	0.5	—	1.0	V
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

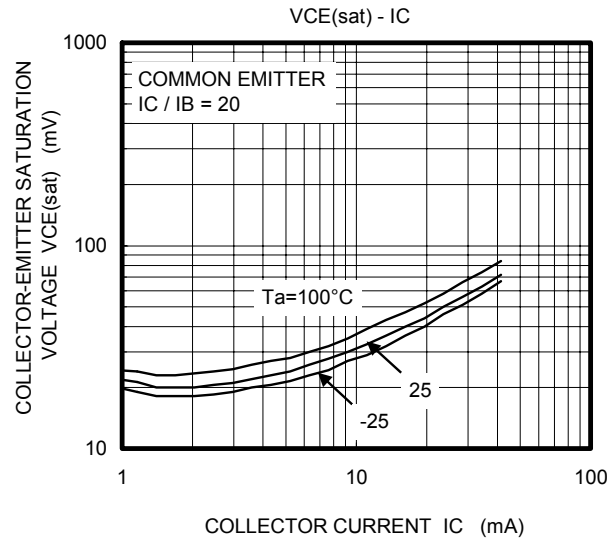
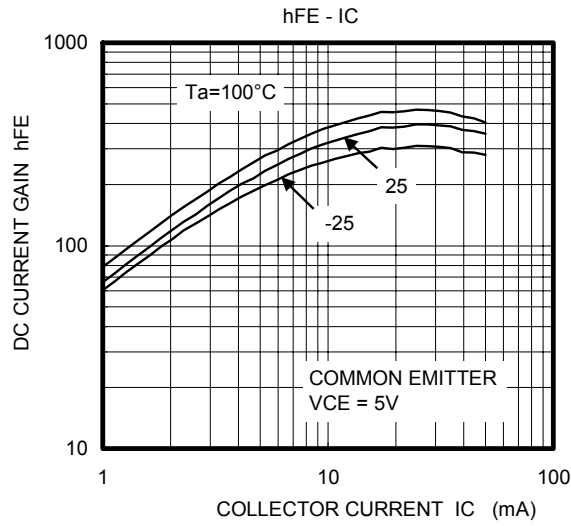
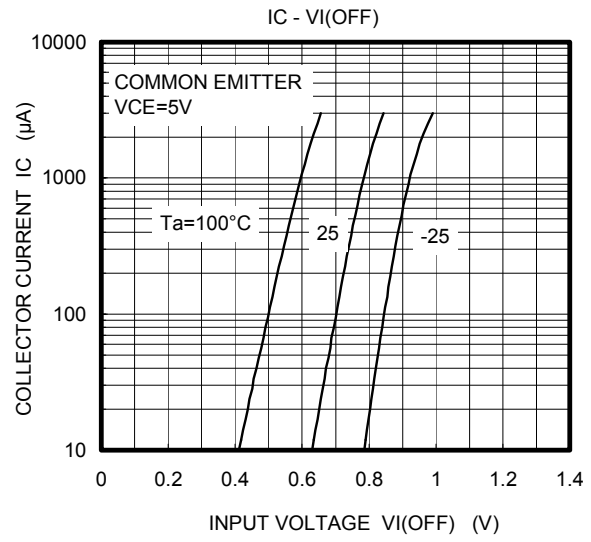
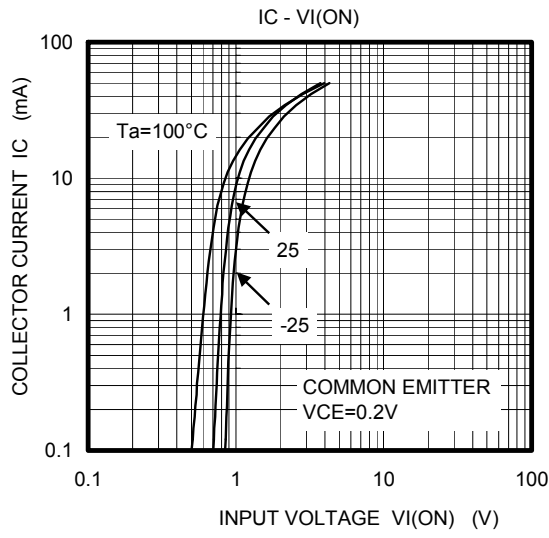
## Electrical Characteristics (Ta = 25°C) (Q2)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20\text{ V}, I_E = 0$	—	—	-100	nA
	$I_{CEO}$	$V_{CE} = -20\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6\text{ V}, I_C = 0$	-0.088	—	-0.131	mA
DC current gain	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	120	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	—	-0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-0.7	—	-1.5	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-0.5	—	-1.0	V
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

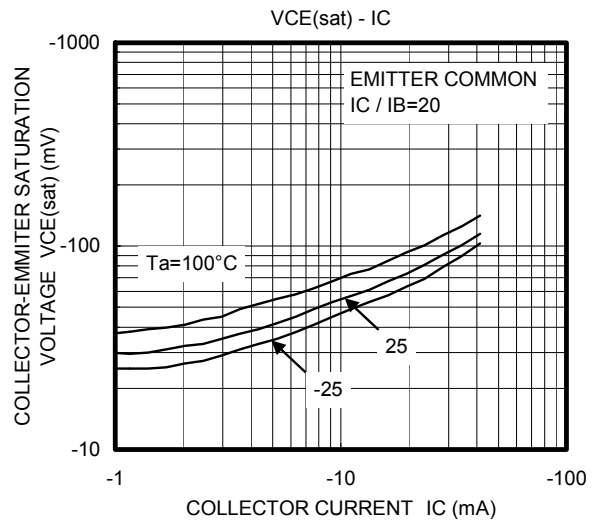
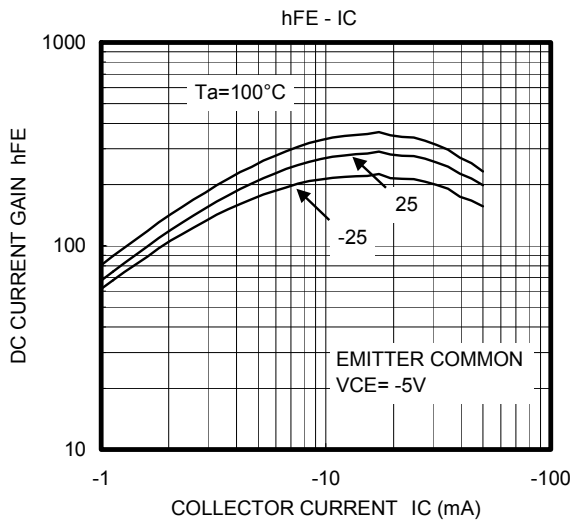
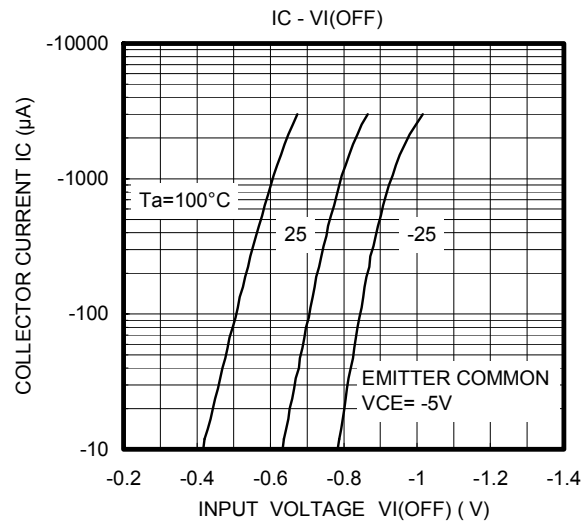
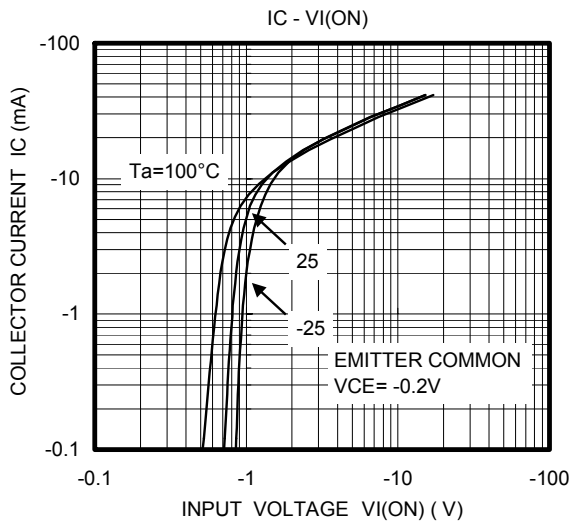
## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	8	10	12	kΩ
Resistor ratio	R1/R2	—	0.17	0.213	0.255	

Q1



Q2



**HANDLING PRECAUTION**

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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